MOSFETs Silicon N-Channel MOS (U-MOSVI-H)

TK50P03M1

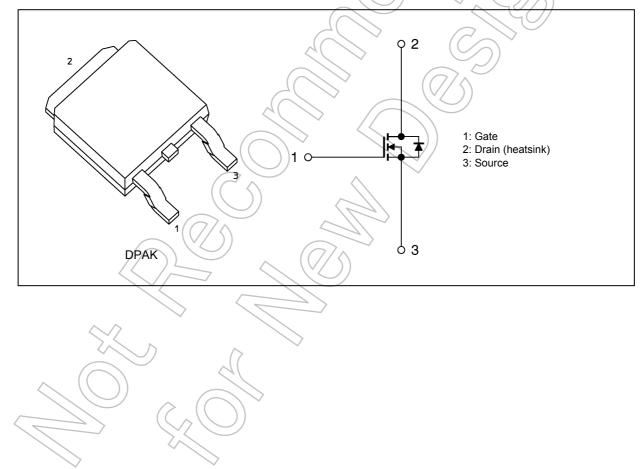
1. Applications

- Switching Voltage Regulators
- Motor Drivers
- Power Management Switches

2. Features

- (1) High-speed switching
- (2) Low gate charge: $Q_{SW} = 8.2 \text{ nC}$ (typ.)
- (3) Low drain-source on-resistance: $R_{DS(ON)} = 5.8 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (4) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 30 \ V)$
- (5) Enhancement mode: $V_{th} = 1.3$ to 2.3 V ($V_{DS} = 10$ V, $I_D = 0.2$ mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			V _{DSS}	30	V
Gate-source voltage			V _{GSS}	±20	
Drain current (DC)		(Note 1)	I _D	50	А
Drain current (pulsed)		(Note 1)	I _{DP}	150	
Power dissipation	(T _c = 25°C)		PD	47	W
Single-pulse avalanche energy		(Note 2)	E _{AS}	65	mJ
Single-pulse avalanche current			I _{AS}	50	А
Channel temperature		4	T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

	Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	$\langle \langle \rangle$	R _{th(ch-c)}	2.65	°C/W
Channel-to-ambient thermal resistance	$\langle \rangle$	R _{th(ch-a)}	125	

Note 1: Ensure that the channel temperature does not exceed 150°C. Note 2: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 20 µH, R_G = 25 Ω , I_{AS} = 50 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

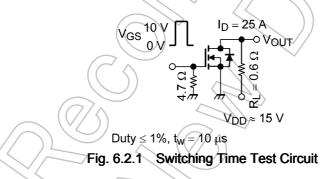
6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V			±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	\langle		10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	30		—	V
	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	15	$\langle \gamma \rangle$	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.2 mA	1.3	2_	2.3	
Drain-source on-resistance	R _{DS(ON)}	$V_{GS} = 4.5 V, I_D = 25 A$	$V \uparrow$	7.5	9.8	mΩ
		V _{GS} = 10 V, I _D = 25 A	9	5.8	7.5	

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	- [21700	_	pF
Reverse transfer capacitance	C _{rss}		_((125	_	
Output capacitance	C _{oss}		R	380) —	
Gate resistance	r _g	V _{DS} = 10 V, V _{GS} = 0 V, f = 5 MHz	$\sim -$	1.2	3.3	Ω
Switching time (rise time)	tr	See Figure 6.2.1.		20	_	ns
Switching time (turn-on time)	t _{on}		~_]	25	_	
Switching time (fall time)	t _f			22		
Switching time (turn-off time)	t _{off}		<u> </u>	64	_	



6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

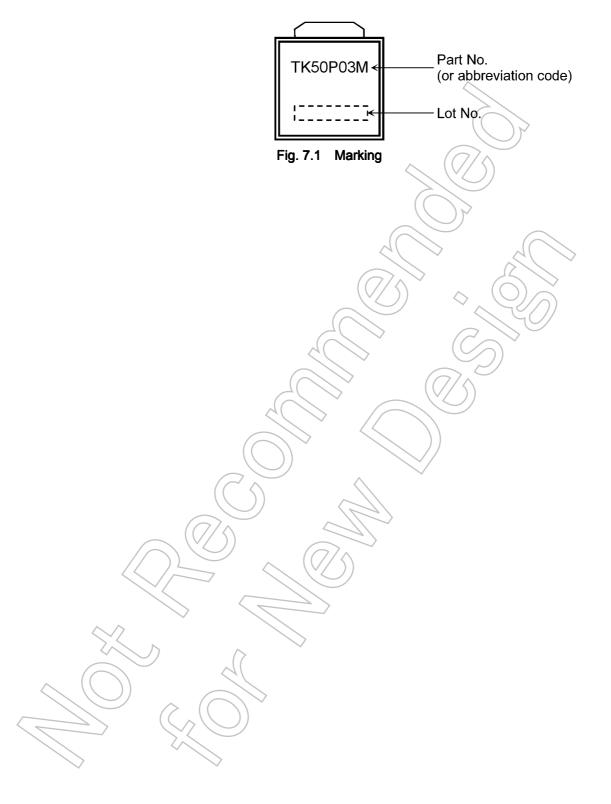
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus		$V_{DD}\approx 24$ V, V_{GS} = 10 V, I_{D} = 50 A		25.3	_	nC
gate-drain)		$V_{DD}\approx 24~V,~V_{GS}$ = 5 V, I _D = 50 A		13.3		
Gate-source charge 1	Q _{gs1}	$V_{DD}\approx 24~V,~V_{GS}\text{ = }10~V,~I_{D}\text{ = }50~A$		6.3	_	
Gate-drain charge	Q _{gd}			4.6	_	
Gate switch charge	Q _{SW}			8.2		

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

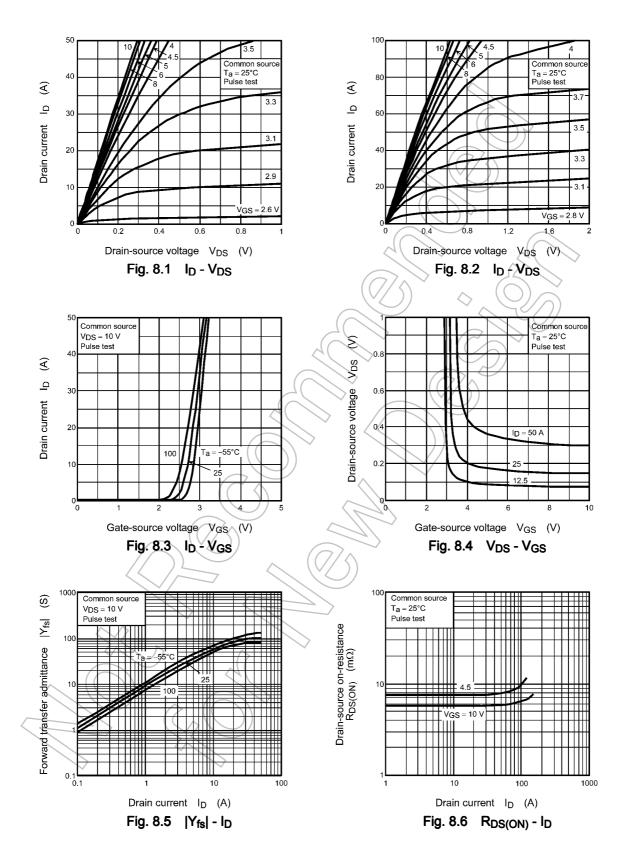
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 3)	I _{DRP}	—	_	_	150	А
Diode forward voltage		V _{DSF}	I _{DR} = 50 A, V _{GS} = 0 V	_	_	-1.2	V

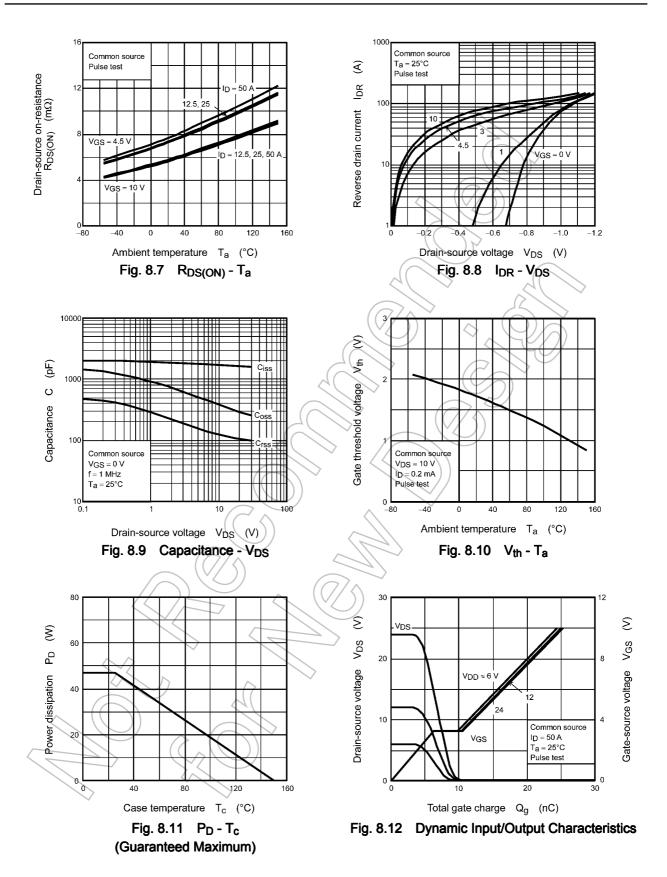
Note 3: Ensure that the channel temperature does not exceed 150°C.

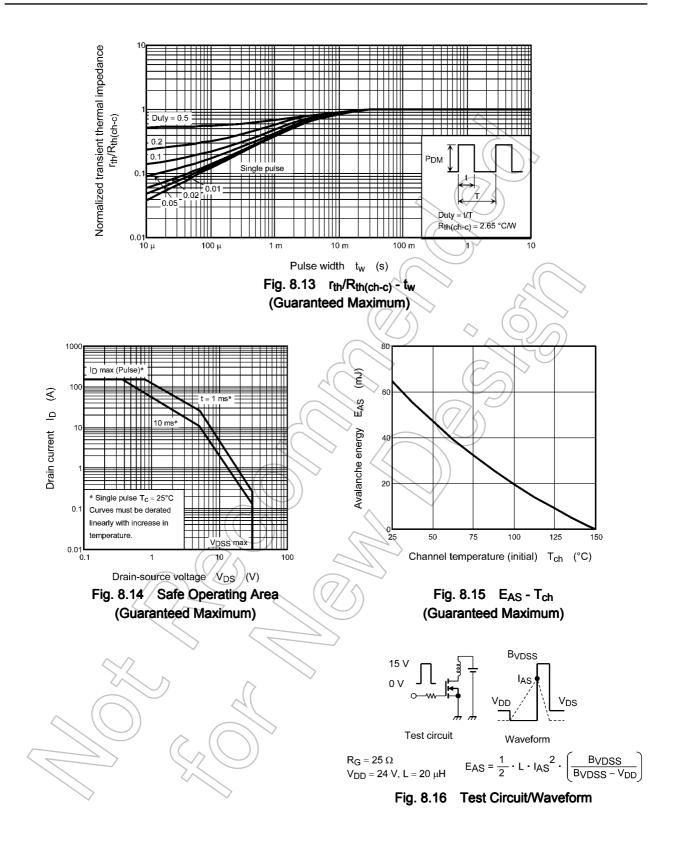
7. Marking



8. Characteristics Curves (Note)





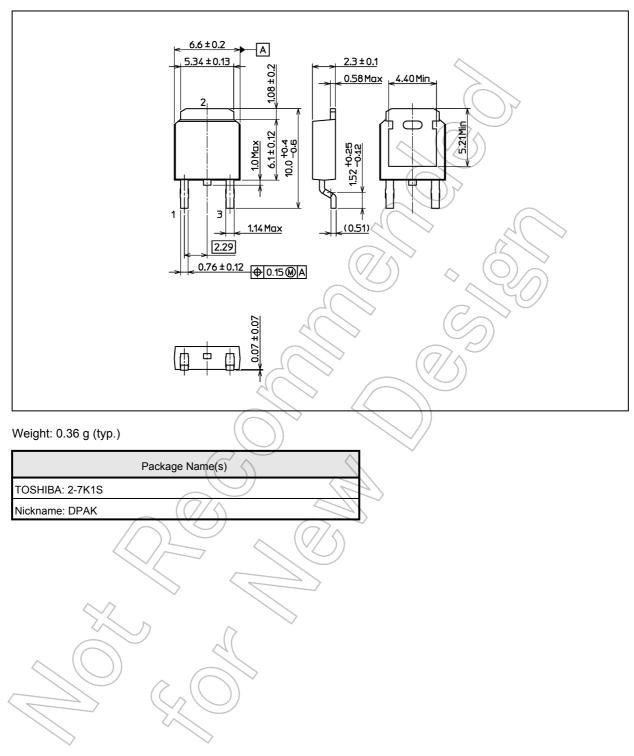


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

TK50P03M1

Package Dimensions

Unit: mm



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